

Please cancel the previous versions of claims 5, 6, 7, and 8, and rewrite them as follows. Pursuant to 37 C.F.R. 1.121, the following are clean copies of the rewritten claims. Marked-up versions of claims 5, 6, 7, and 8 are attached as separate sheets.

5. A method of using a pressure sensitive adhesive sheet comprising sticking the pressure sensitive adhesive sheet to a surface of an adherend that has a surface having a height difference of at least 30 μm and working the adherend at its back while protecting the adherend surface by means of the pressure sensitive adhesive sheet, wherein the pressure sensitive adhesive sheet comprises a substrate and, superimposed thereon, a pressure sensitive adhesive layer, said substrate exhibiting a maximum value of dynamic viscoelasticity $\tan \delta$ of 0.78 to 1.61 at a temperature ranging from -5 to 80°C.

6. A method of using a pressure sensitive adhesive sheet comprising sticking the pressure sensitive adhesive sheet to a surface of an adherend that has a surface having a height difference of at least 30 μm and working the adherend at its back while protecting the adherend surface by means of the pressure sensitive adhesive sheet, wherein the pressure sensitive adhesive sheet comprises a substrate and, superimposed thereon, a pressure sensitive adhesive layer, said substrate having a thickness and Young's modulus whose product is in the range of 0.5 to 100 kg/cm and said substrate exhibiting a maximum value of dynamic viscoelasticity $\tan \delta$ of 0.78 to 1.61 at a temperature ranging from -5 to 80°C.

7. A method of using a pressure sensitive adhesive sheet comprising sticking the pressure sensitive adhesive sheet to a surface of a semiconductor wafer which has a surface having a height difference of at least 30 μm and working the semiconductor wafer surface by grinding the back of the semiconductor wafer while protecting the semiconductor wafer surface by means of the pressure sensitive adhesive sheet, wherein the pressure sensitive adhesive sheet comprises a substrate and, superimposed thereon, a pressure sensitive adhesive layer, said substrate exhibiting a maximum value of dynamic viscoelasticity $\tan \delta$ of 0.78 to 1.61 at a temperature ranging from -5 to 80°C.

8. A method of using a pressure sensitive adhesive sheet comprising sticking the pressure sensitive adhesive sheet to a surface of a semiconductor wafer which has a surface having a height difference of at least 30 μm and working the semiconductor wafer surface by